

SHEET 1 OF 11
CHU ET AL.
YOR920010308US1 RMT

Ge Concentration (atoms/cc)

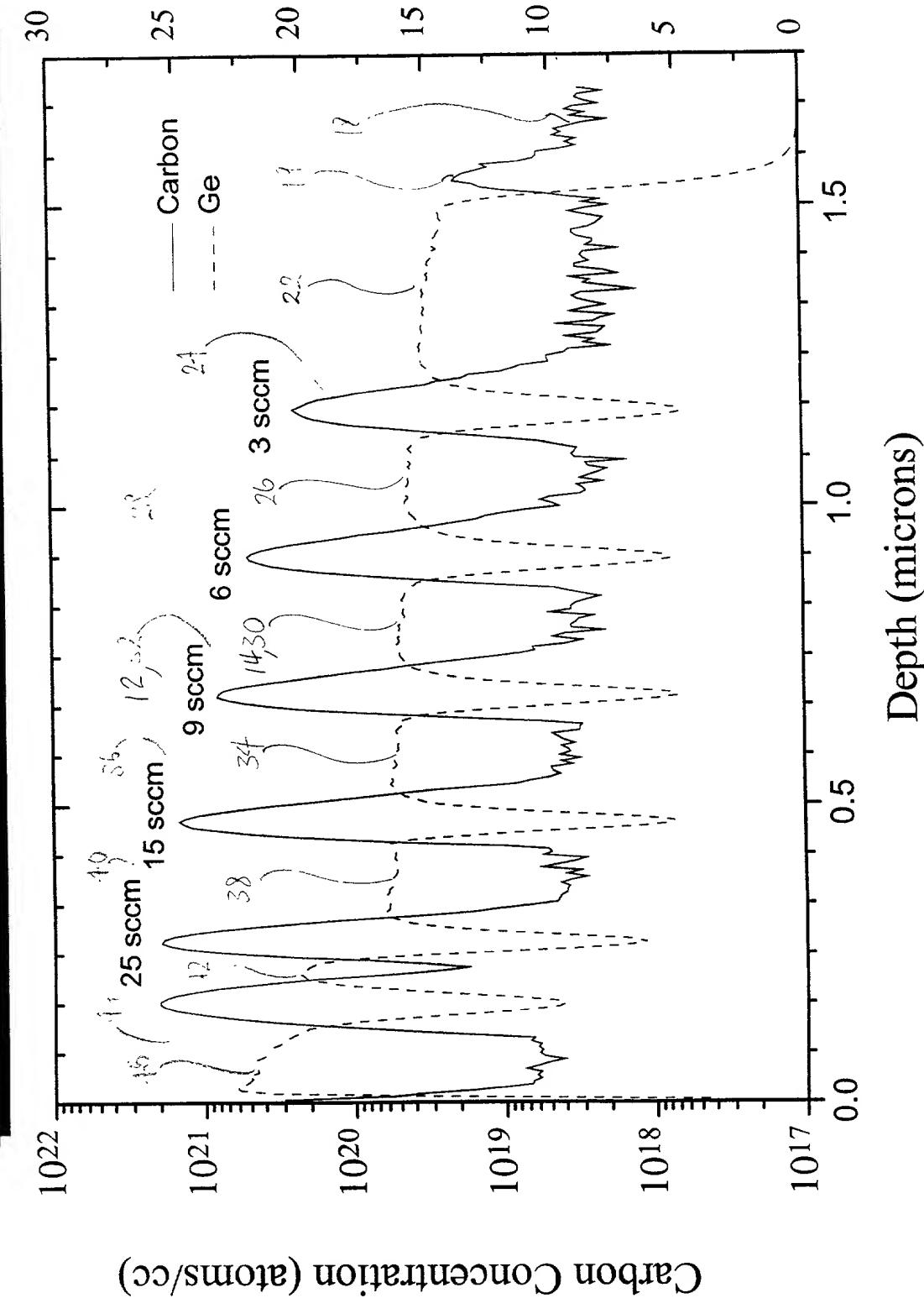


Figure 1

Carbon-30: UHV-CVD SIB.C @500C w/ 2% C₂H₄/He

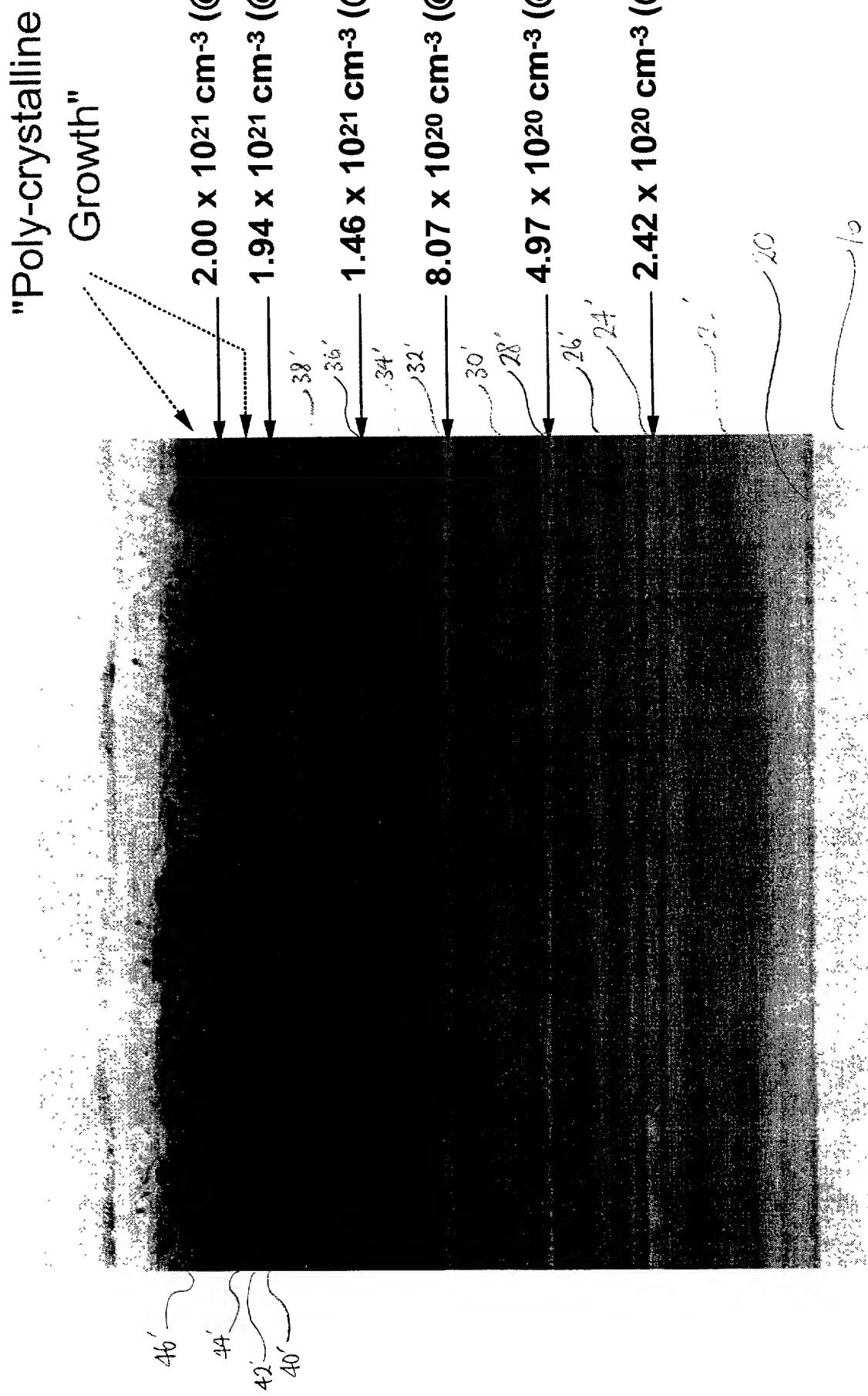


Figure 9

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Ge Concentration (atomic percent)

Carbon-32 UHV-CVD SiGe:C using 2% C_2H_2 / 4% He

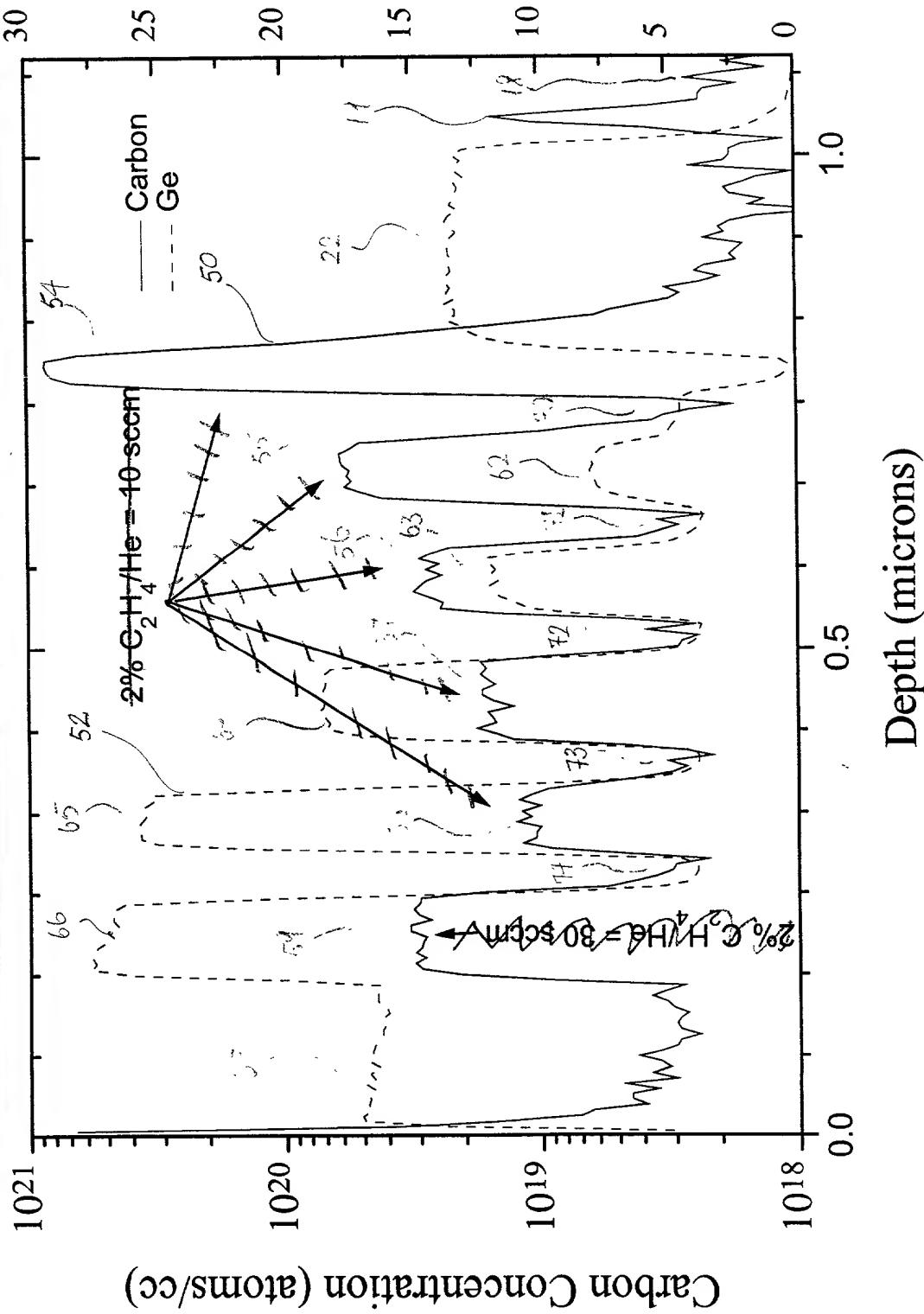


Figure 3

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Ge Concentration (atomic percent)

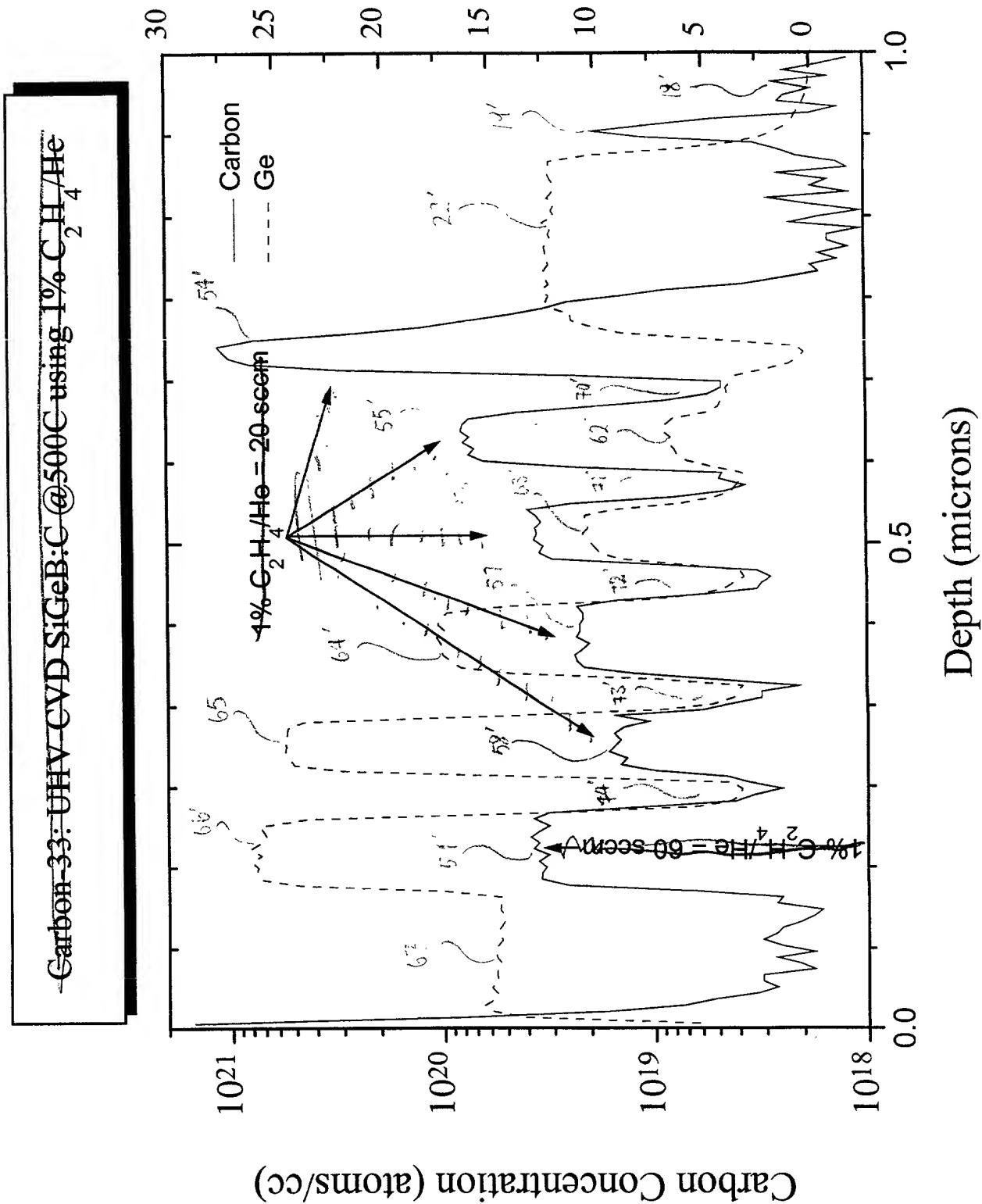


Figure 4

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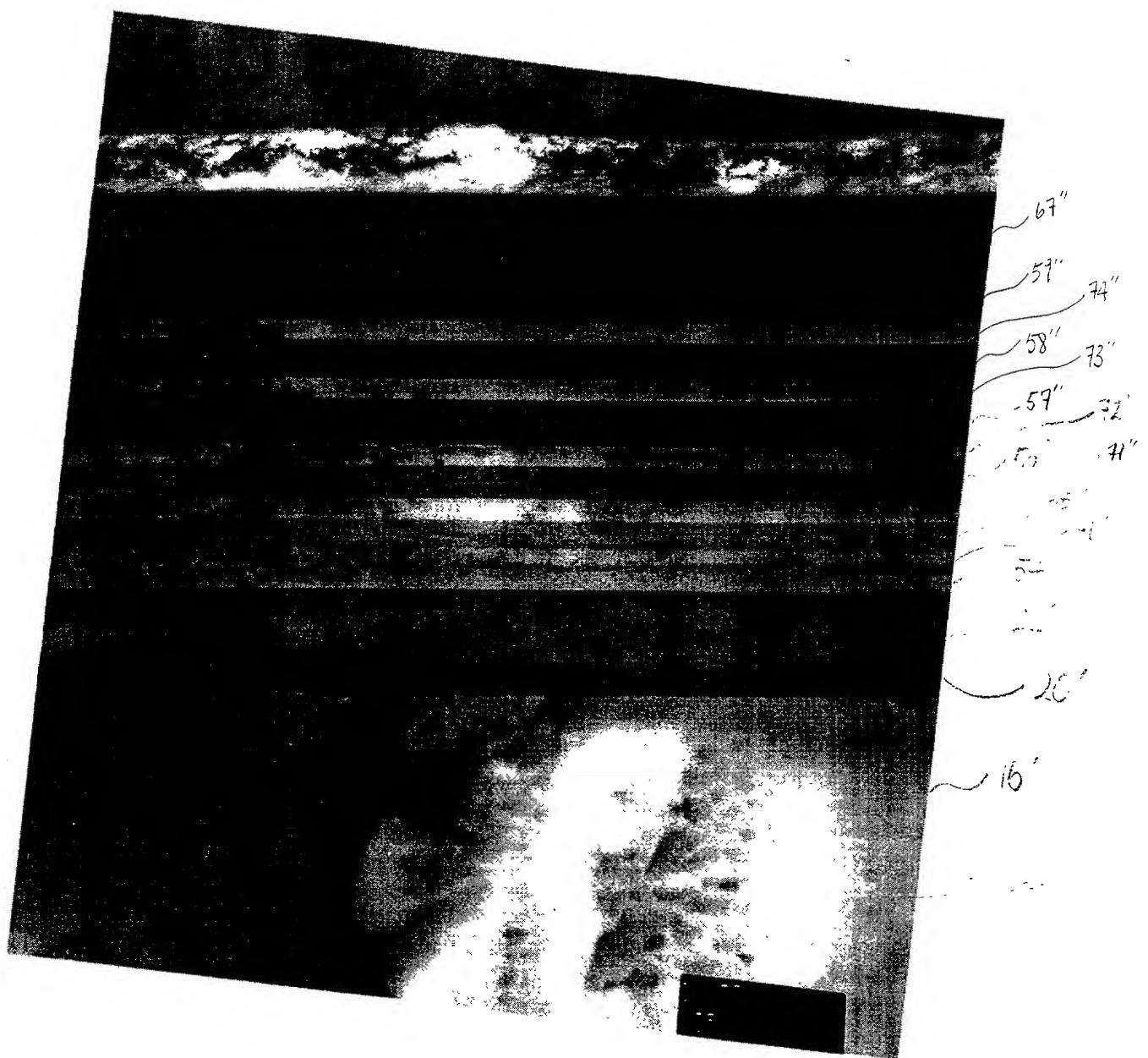


Figure 5

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Ge Concentration (atoms percent)

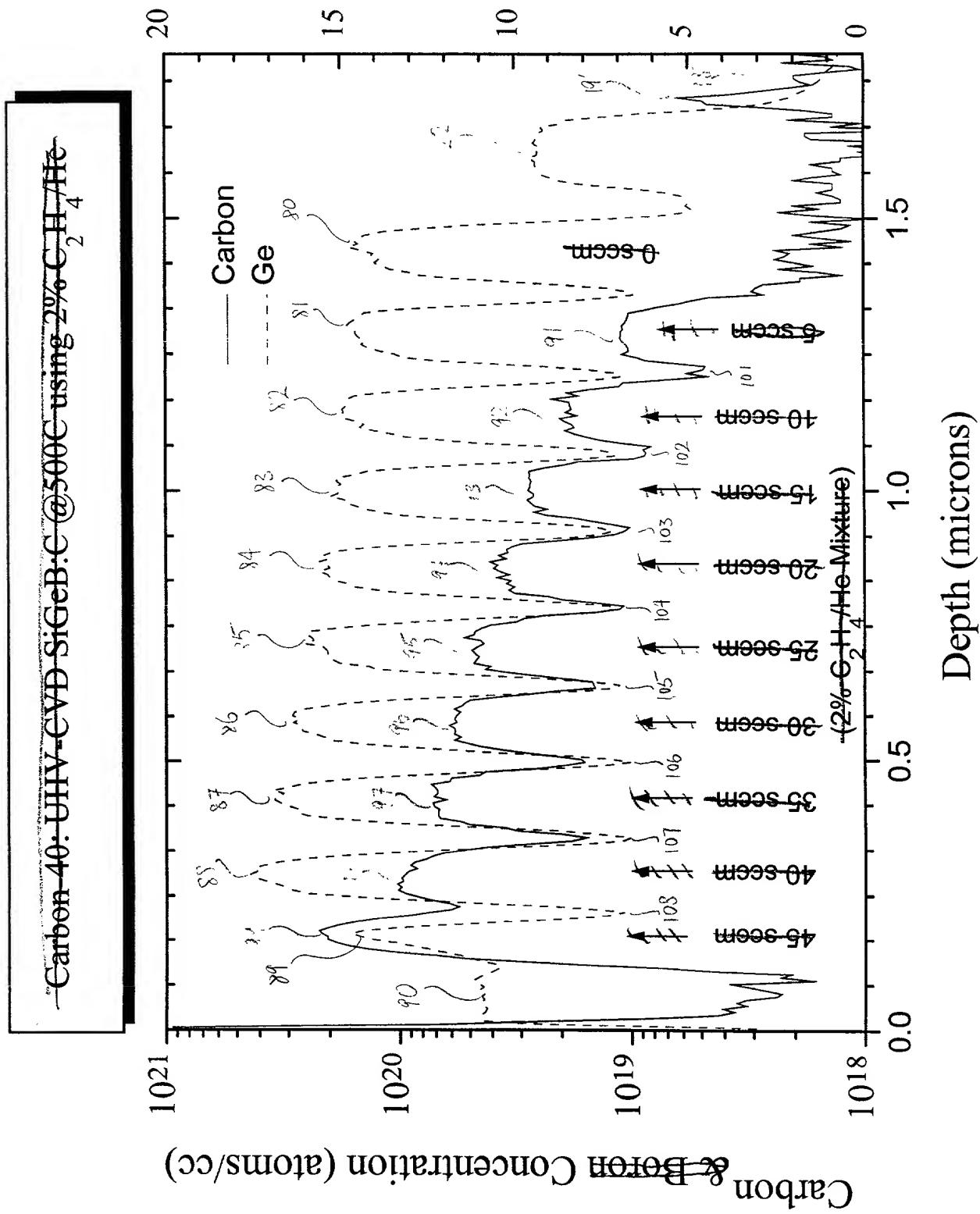
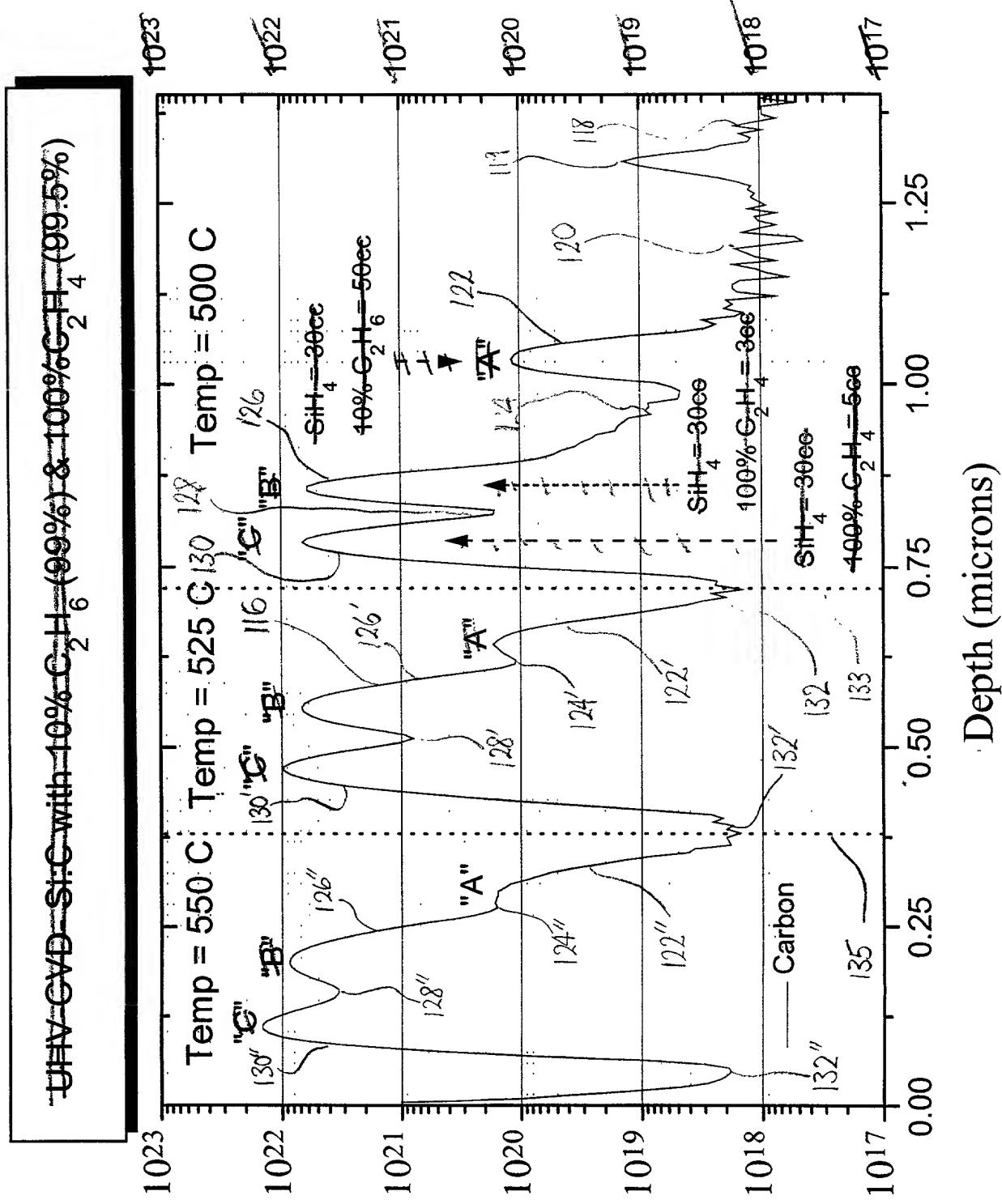
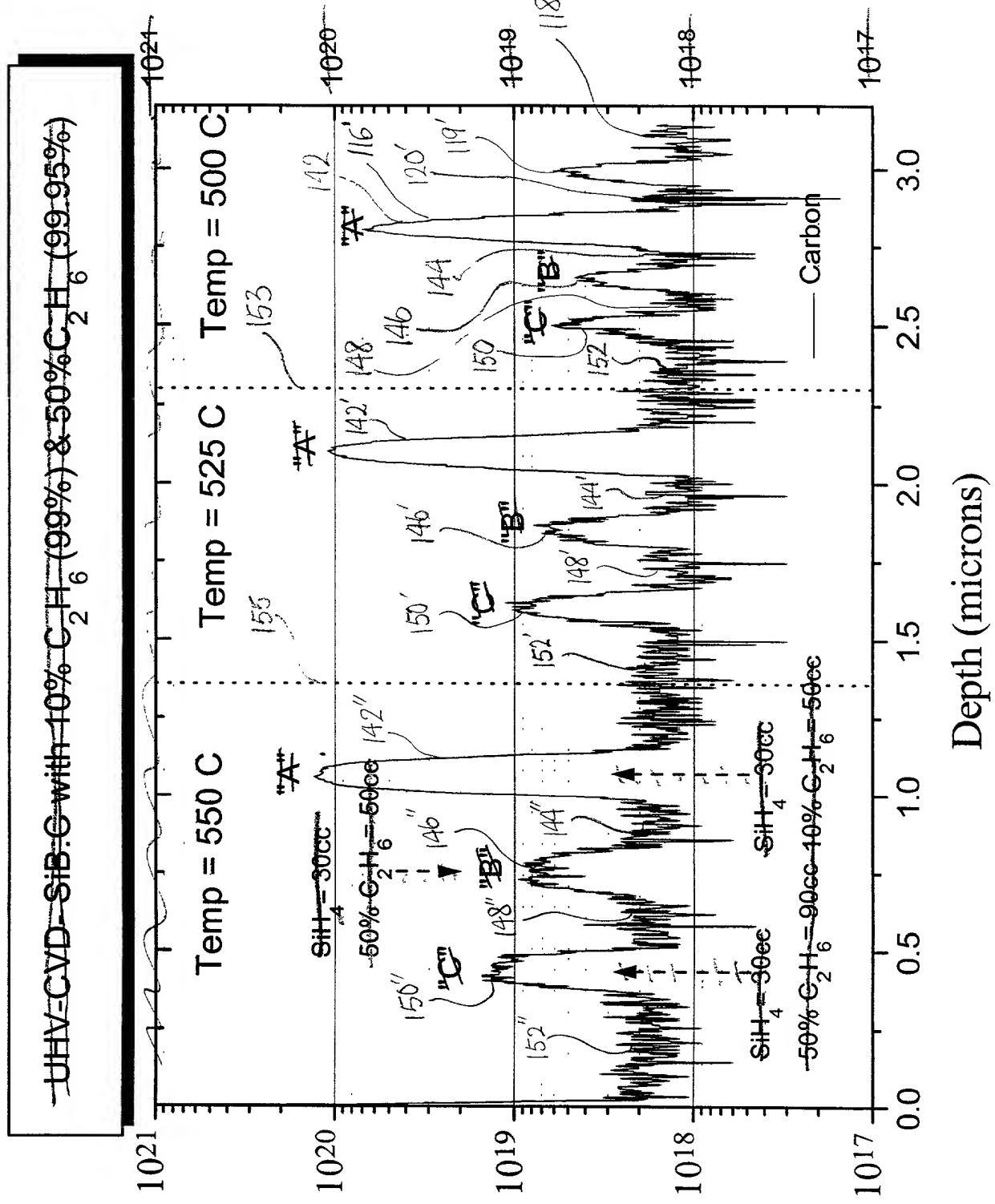


Figure 6



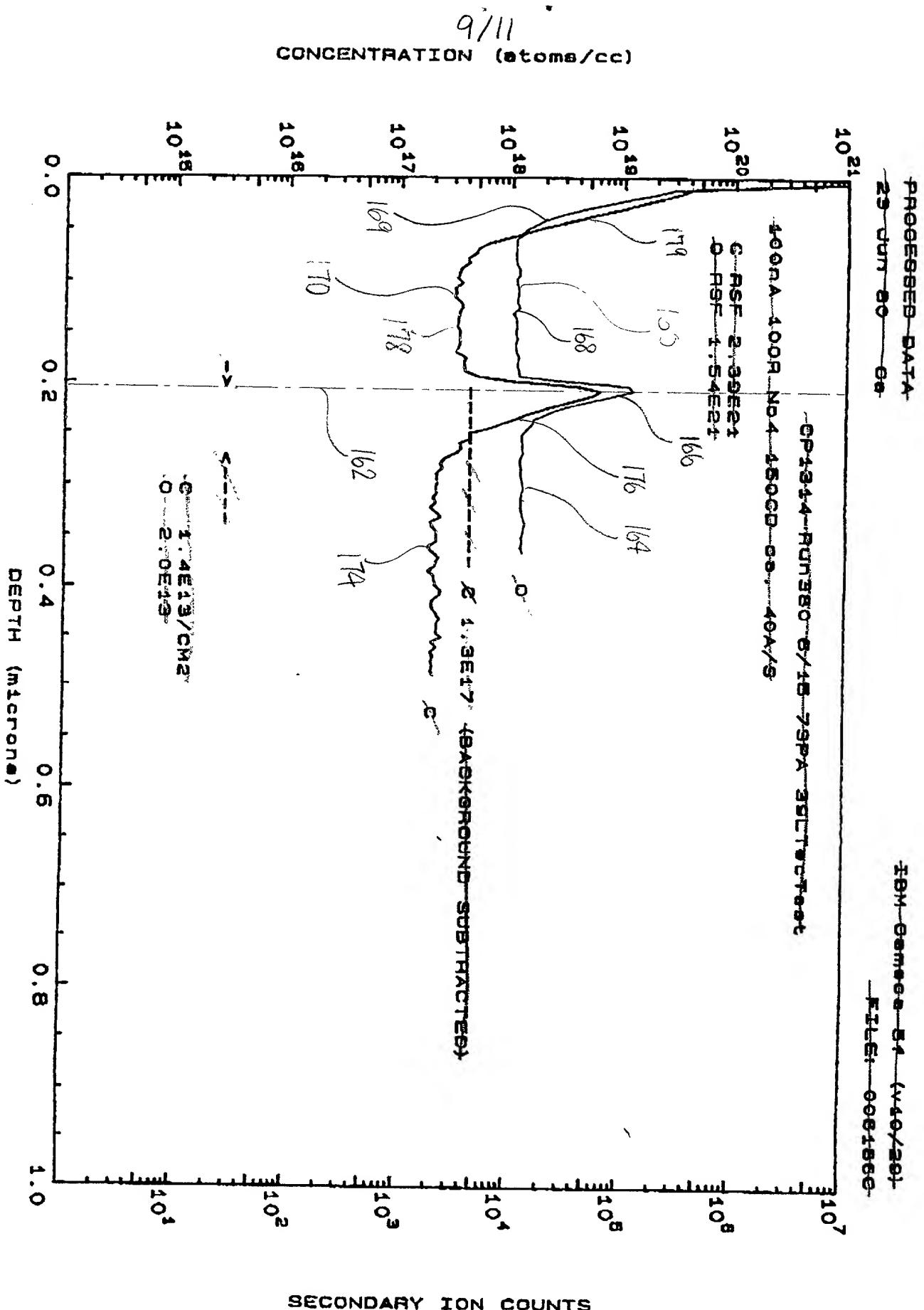
Carbon Concentration (atoms/cc)

Figure 7

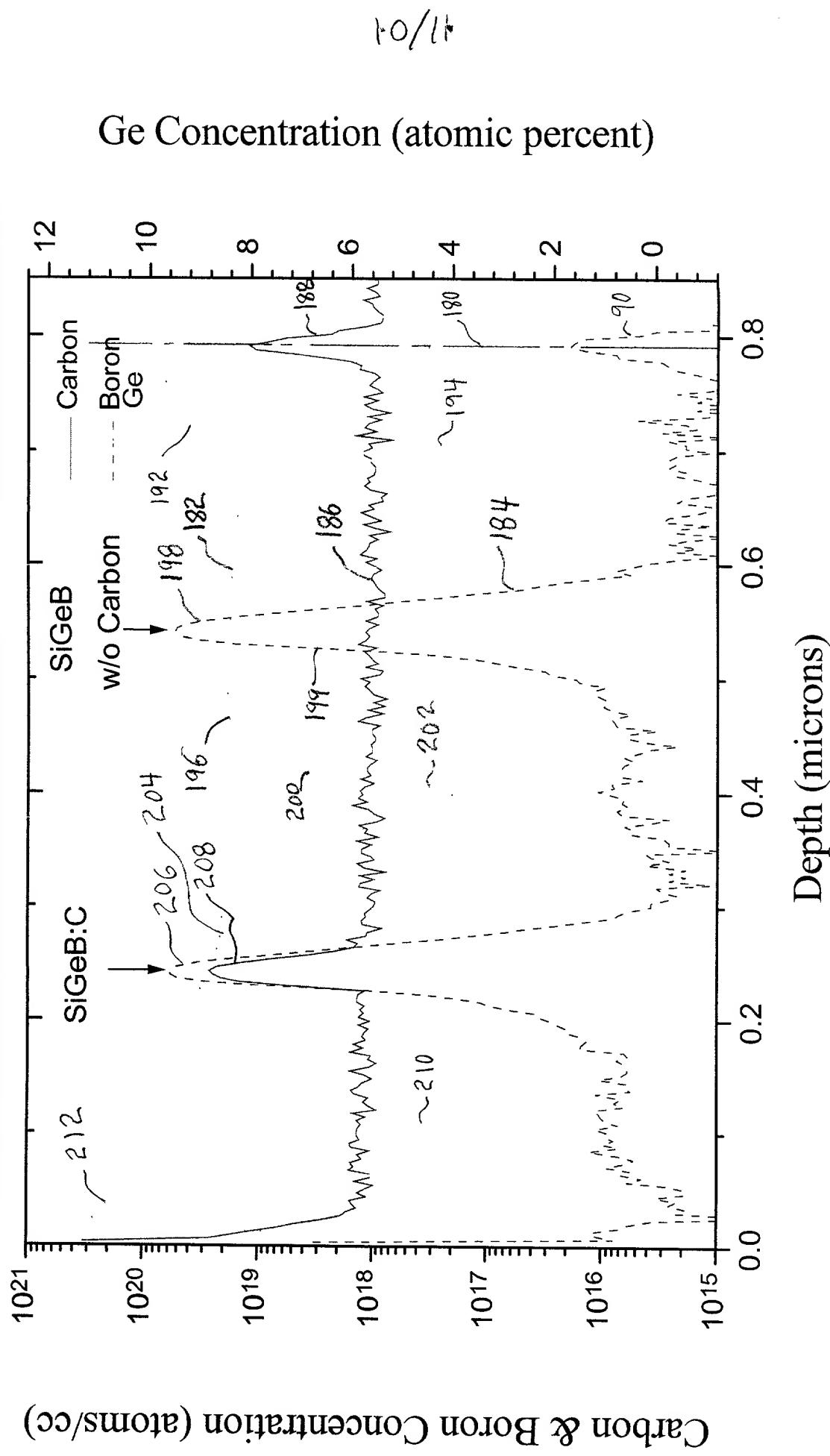


Carbon Concentration (atoms/cc)

Figure 8.



Carbon-13: UHV-CVD SiGeB:C at 550°C (C₂H₄)ⁿ As Growth



Impact of Carbon on SiGeB Layers after "850°C Furnace Anneal"

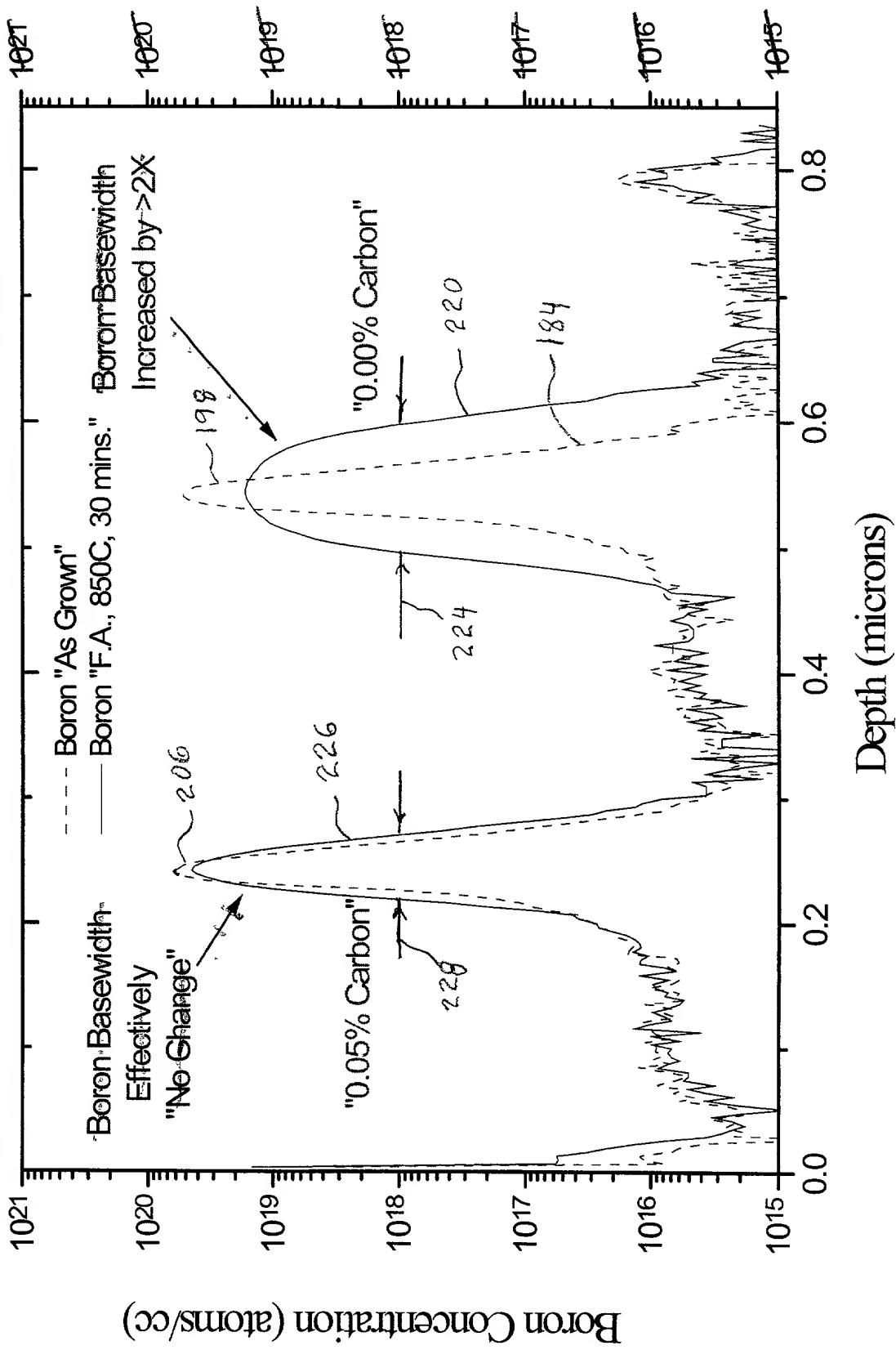


Figure 11